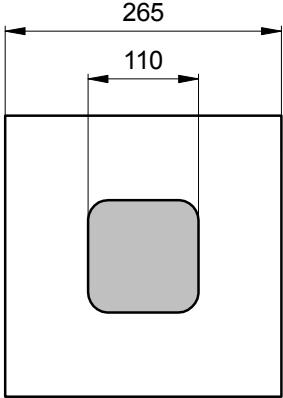


Radiation	Type	Technology	Electrodes
Yellow-green	Standard	AlInGaP/GaAs	P (anode) up

	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 (±20) μm <u>anode</u> gold alloy, 1.5 μm <u>cathode</u> gold alloy, 0.5 μm dotted, 25% covered	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		2.0	2.4	V
Reverse voltage	I _R = 10 μA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	0.09	0.12		mW
Radiant power ²	I _F = 20 mA	Φ _e		0.23		mW
Luminous intensity ¹	I _F = 20 mA	I _v	12	20		mcd
Luminous intensity ²	I _F = 20 mA	I _v		38		mcd
Peak wavelength	I _F = 20 mA	λ _p	568	572	577	nm
Dominant wavelength	I _F = 20 mA	λ _D		572		nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		15		nm
Switching time	I _F = 20 mA	t _r , t _f		30/20		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I _v (typ) [mcd]	V _F (typ) [V]	Quantity
ELC-572-13				

Packing: Chips on adhesive film with wire-bond side on top